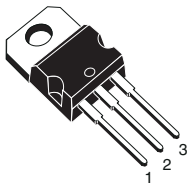
STB80NF10
STP80NF10

N-channel 100 V, 0.012 Ω, 80 A, TO-220, D²PAK low gate charge STripFET™ II Power MOSFET

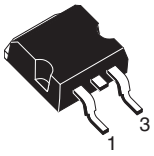
Features

Type	V_{DSS}	$R_{DS(on)}$ max	I_D
STP80NF10	100 V	< 0.015 Ω	80 A
STB80NF10	100 V	< 0.015 Ω	80 A

- Exceptional dv/dt capability
- 100% Avalanche tested
- Application oriented characterization



TO-220



D²PAK

Applications

- Switching applications

Description

This Power MOSFET series realized with STMicroelectronics unique STripFET process has specifically been designed to minimize input capacitance and gate charge. It is therefore suitable as primary switch in advanced high-efficiency isolated DC-DC converters for telecom and computer application. It is also intended for any application with low gate charge drive requirements.

Figure 1. Internal schematic diagram

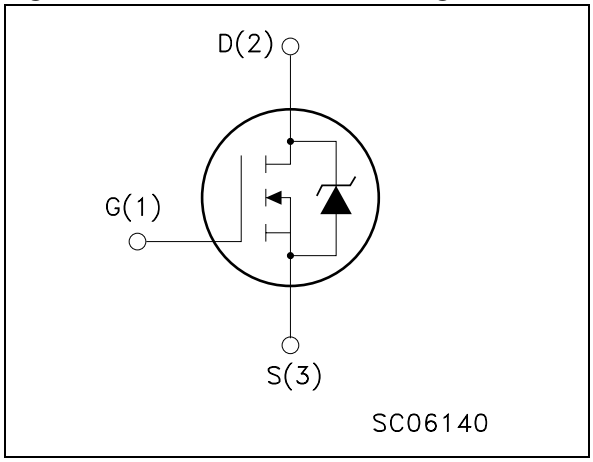


Table 1. Device summary

Order codes	Marking	Package	Packaging
STP80NF10	P80NF10@	TO-220	Tube
STB80NF10T4	B80NF10@	D²PAK	Tape and reel

Contents

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage (V_{GS} = 0)	100	V
V_{GS}	Gate- source voltage	±20	V
I_D (1)	Drain current (continuous) at T_C = 25 °C	80	A
I_D (1)	Drain current (continuous) at T_C = 100 °C	80	A
I_{DM} (2)	Drain current (pulsed)	320	A
P_{TOT}	Total dissipation at T_C = 25 °C	300	W
	Derating factor	2	W/°C
dv/dt (3)	Peak diode recovery voltage slope	7	V/ns
E_{AS} (4)	Single pulse avalanche energy	350	mJ
T_{stg} T_j	Storage temperature Operating junction temperature	-55 to 175	°C

1. Limited by package
2. Pulse width limited by safe operating area
3. I_{SD} < 80 A, di/dt < 300 A/µs, V_{DD}= 80% $V_{(BR)DSS}$
4. Starting Tj = 25 °C, I_D = 40 A, V_{DD} = 50 V

Table 3. Thermal resistance

Symbol	Parameter	Value	Unit
Rthj-case	Thermal resistance junction-case max	0.5	°C/W
Rthj-amb	Thermal resistance junction-ambient max	62.5	°C/W
T_l	Maximum lead temperature for soldering purpose	300	°C

2 Electrical characteristics

(T_{CASE}=25 °C unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	I_D = 250 µA, V_{GS} = 0	100			V
I_{DSS}	Zero gate voltage drain current (V_{GS} = 0)	V_{DS} = Max rating V_{DS} = Max rating @125°C			500 10	nA µA
I_{GSS}	Gate-body leakage current (V_{DS} = 0)	V_{GS} = ±20 V			±100	nA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 250 µA	2	3	4	V
$R_{DS(on)}$	Static drain-source on resistance	V_{GS} = 10 V, I_D = 40 A		0.012	0.015	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward transconductance	V_{DS} = 25 V , I_D =40 A	-	50		S
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	V_{DS} = 25 V, f = 1 MHz, V_{GS} = 0	-	5500 700 175		pF pF pF
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	V_{DD} = 50 V, I_D = 80 A, V_{GS} = 10 V	-	135 23 51.3	182	nC nC nC

1. Pulsed: pulse duration = 300 µs, duty cycle 1.5%

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	Turn-on delay time Rise time Turn-off-delay time Fall time	V_{DD} = 50 V, I_D= 40 A, R_G = 4.7 Ω, V_{GS}=10 V *(see Figure 15)*	-	26 80 116 60	-	ns ns ns ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
I_{SD}	Source-drain current		-		80	A
I_{SDM} (1)	Source-drain current (pulsed)		-		320	A
V_{SD} (2)	Forward on voltage	I_{SD} = 80 A, V_{GS} = 0	-		1.3	V
t_{rr}	Reverse recovery time	I_{SD}=80 A, V_{DD} = 50 V		106		ns
Q_{rr}	Reverse recovery charge	di/dt = 100 A/µs,	-	450		nC
I_{RRM}	Reverse recovery current	T_j=150 °C		8.5		A

1. Pulse width limited by safe operating area
2. Pulse duration=300µs, duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

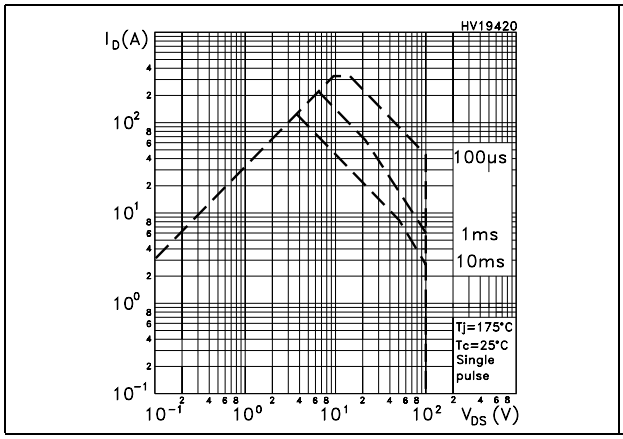


Figure 3. Thermal impedance

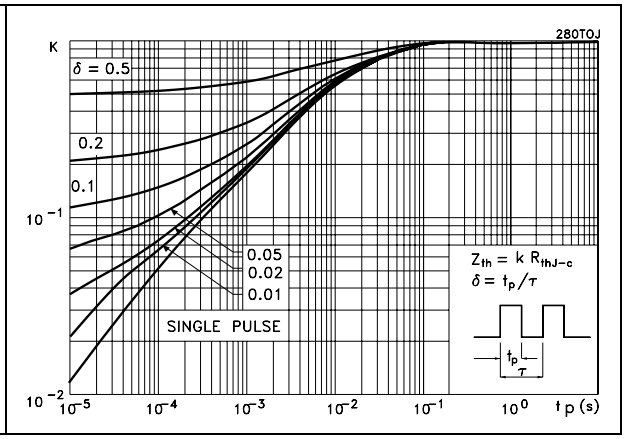


Figure 4. Output characteristics

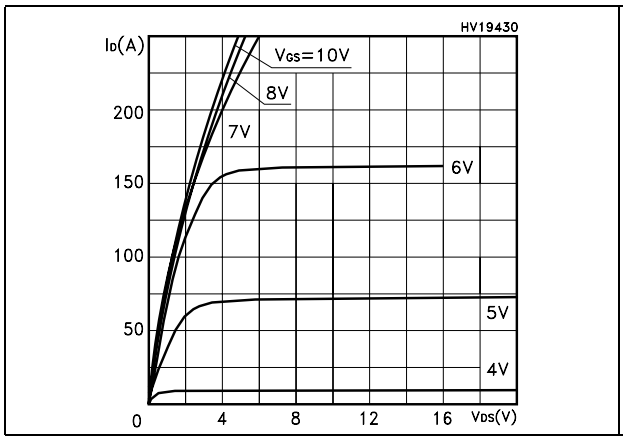


Figure 5. Transfer characteristics

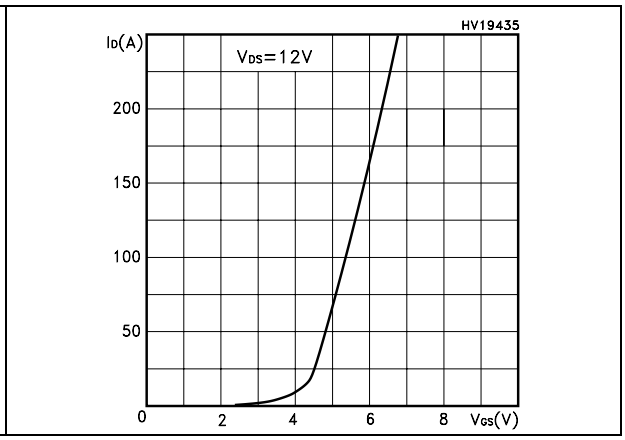


Figure 6. Transconductance

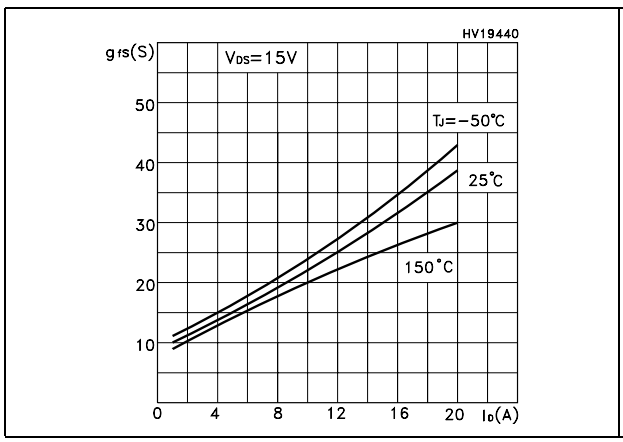


Figure 7. Static drain-source on resistance

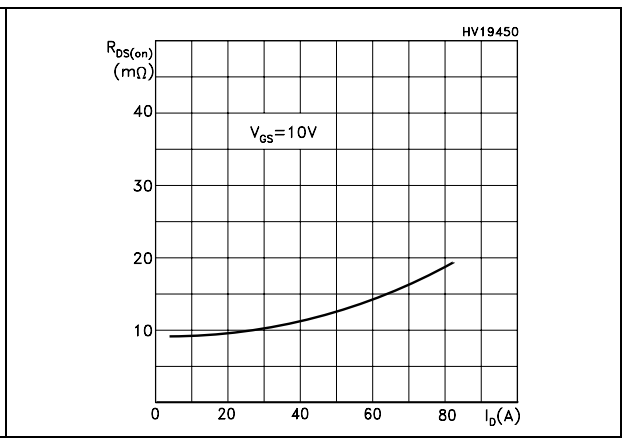


Figure 8. Gate charge vs. gate-source voltage

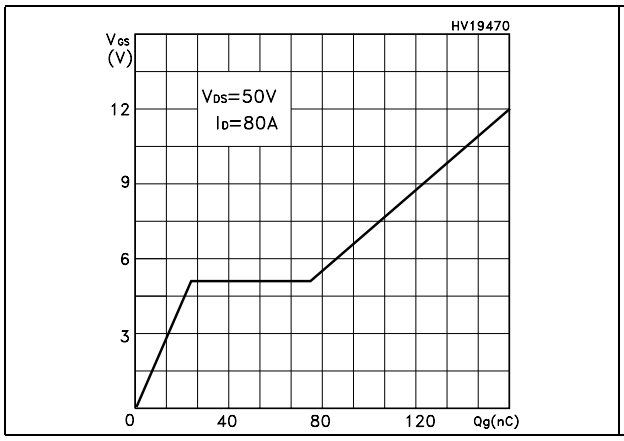


Figure 9. Capacitance variations

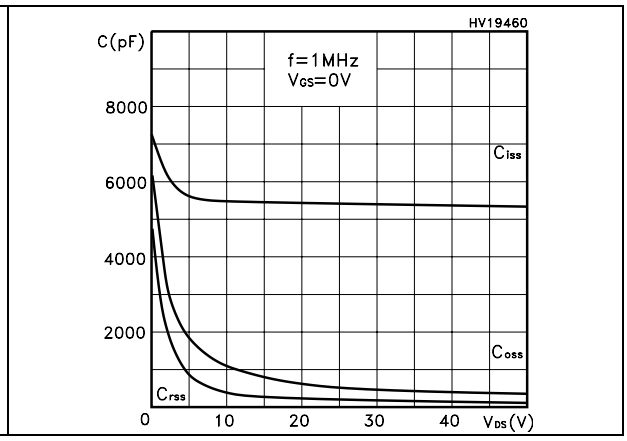


Figure 10. Normalized gate threshold voltage vs. temperature

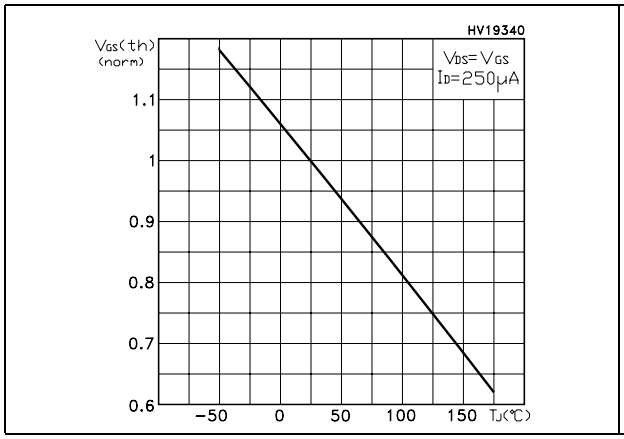


Figure 11. Normalized on resistance vs. temperature

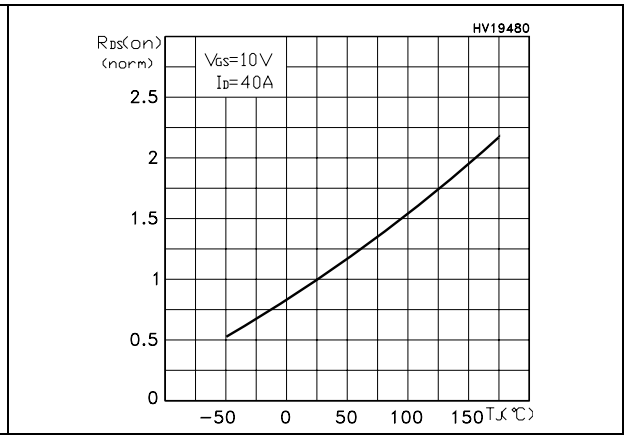
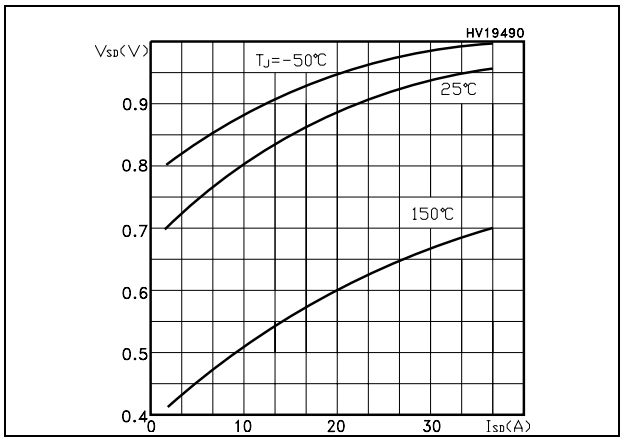


Figure 12. Source-drain diode forward characteristics



3 Test circuits

Figure 13. Switching times test circuit for resistive load

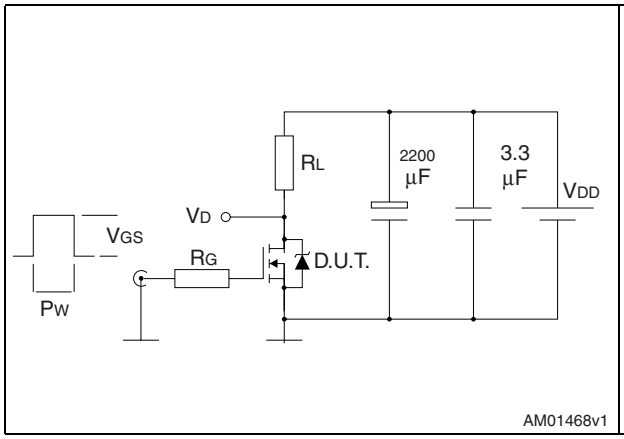


Figure 14. Gate charge test circuit

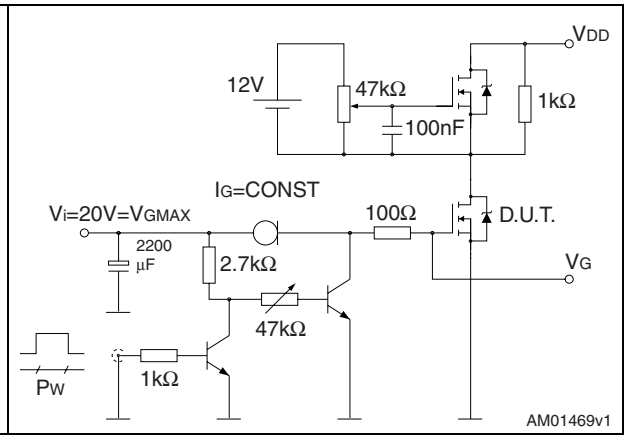


Figure 15. Test circuit for inductive load switching and diode recovery times

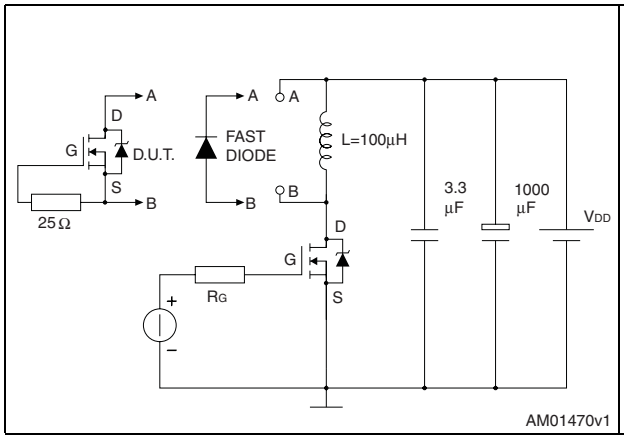


Figure 16. Unclamped inductive load test circuit

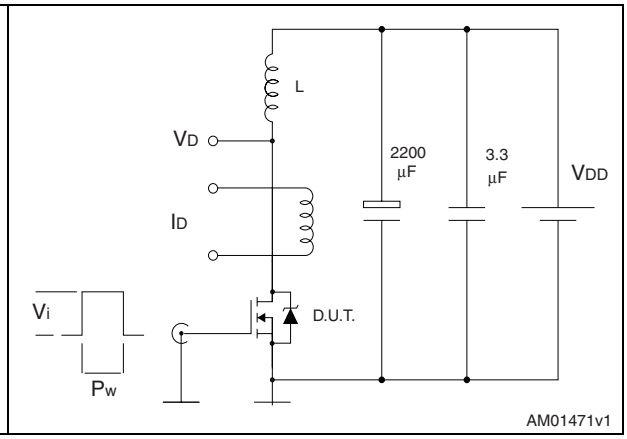


Figure 17. Unclamped inductive waveform

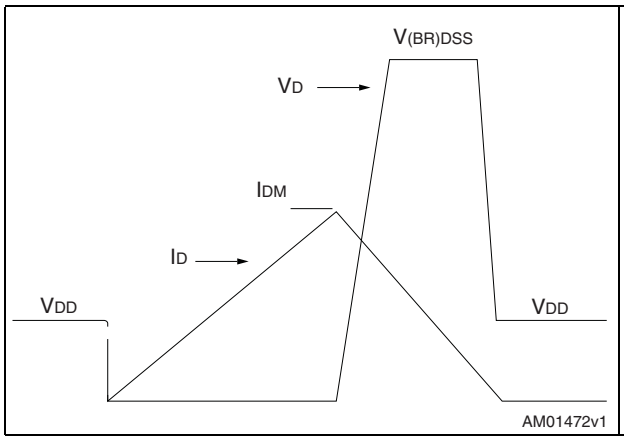
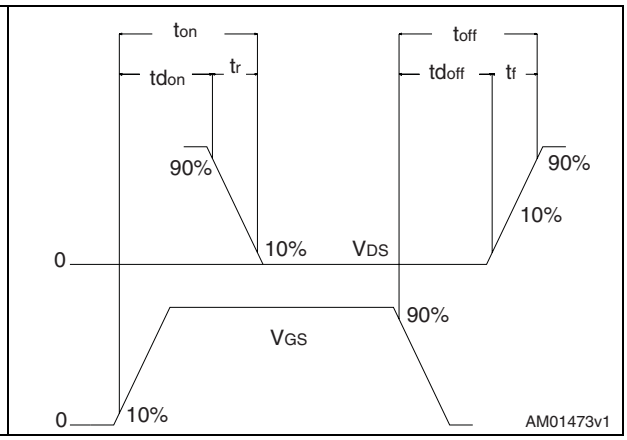


Figure 18. Switching time waveform

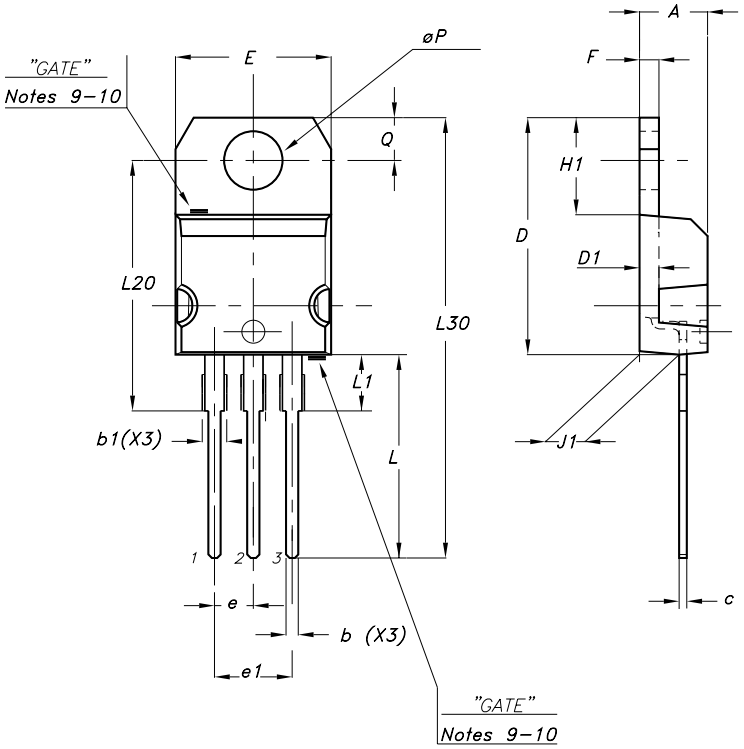


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

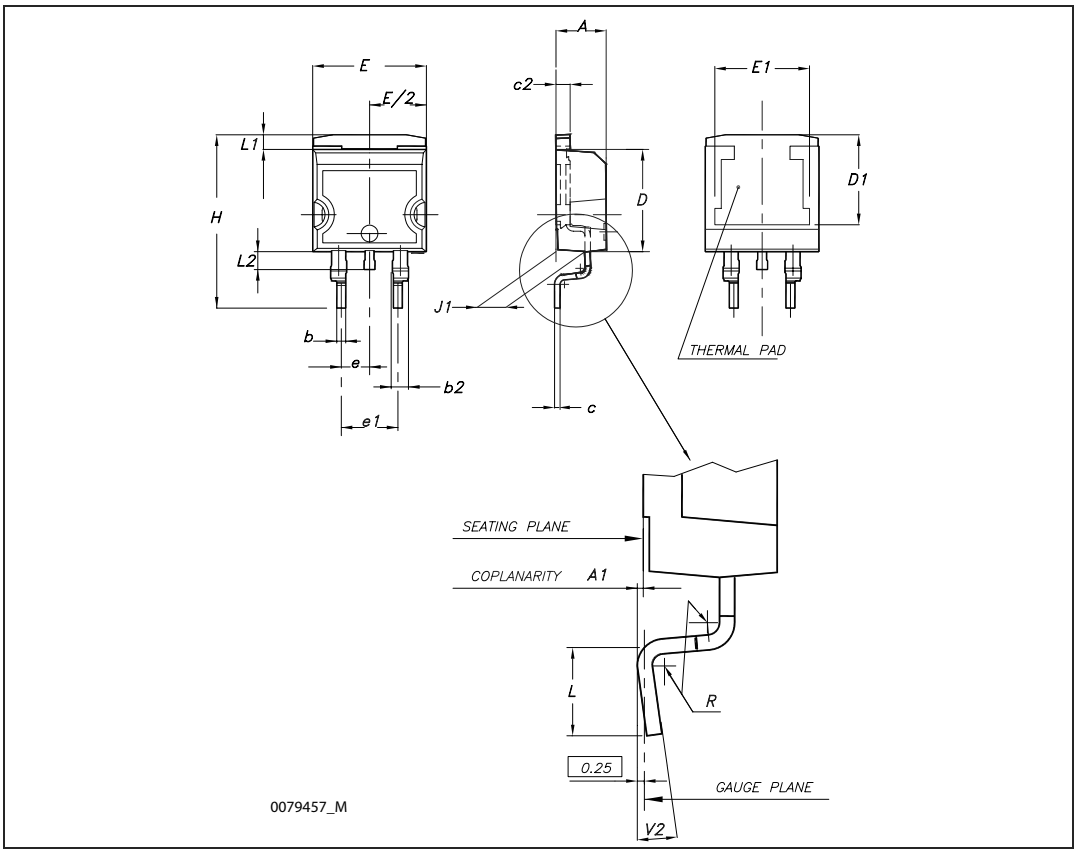
TO-220 mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.48		0.70	0.019		0.027
D	15.25		15.75	0.6		0.62
D1		1.27			0.050	
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.051
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
∅P	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



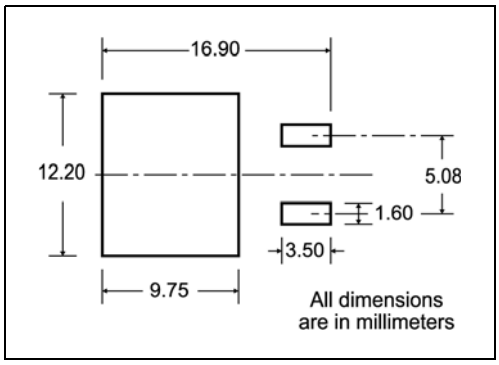
D²PAK (TO-263) mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
A1	0.03		0.23	0.001		0.009
b	0.70		0.93	0.027		0.037
b2	1.14		1.70	0.045		0.067
c	0.45		0.60	0.017		0.024
c2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1	7.50			0.295		
E	10		10.40	0.394		0.409
E1	8.50			0.334		
e		2.54			0.1	
e1	4.88		5.28	0.192		0.208
H	15		15.85	0.590		0.624
J1	2.49		2.69	0.099		0.106
L	2.29		2.79	0.090		0.110
L1	1.27		1.40	0.05		0.055
L2	1.30		1.75	0.051		0.069
R		0.4			0.016	
V2	0°		8°	0°		8°

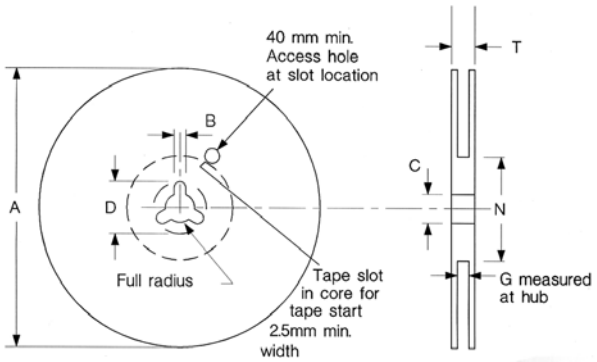


5 Packaging mechanical data

D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT



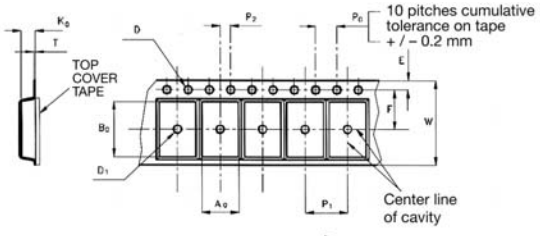
REEL MECHANICAL DATA

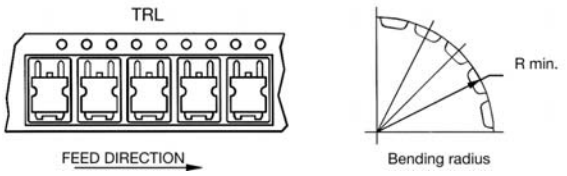
DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

BASE QTY	BULK QTY
1000	1000

TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956





* on sales type

6 Revision history

Table 8. Document revision history

Date	Revision	Changes
04-Nov-2003	8	New datasheet according to PCN DSG-TRA/03/382
13-Dec-2004	9	D²PAK inserted
16-Dec-2004	10	@ inserted in table 2 for TO-220 marking
27-Jan-2005	11	New value in table 3
22-Feb-2005	12	Id value changed
28-Feb-2005	13	New value in table 3
01-Mar-2005	14	Vgs value changed
06-Apr-2006	15	The document has been reformatted
25-Jan-2007	16	Typo mistake on page 1 (order codes)
17-Nov-2008	17	E_{AS} value has been updated
15-Apr-2009	18	I_{DSS} value changed in *Table 4: On/off states*

Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries (“ST”) reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST’s terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST’S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY AN AUTHORIZED ST REPRESENTATIVE, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER’S OWN RISK.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Philippines - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com